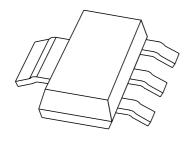
DISCRETE SEMICONDUCTORS

DATA SHEET



BF721; **BF723**PNP high-voltage transistors

Product specification Supersedes data of September 1994 File under Discrete Semiconductors, SC04 1996 Dec 05





PNP high-voltage transistors

BF721 has been discontinued

BF721; BF723

FEATURES

• Low feedback capacitance.

APPLICATIONS

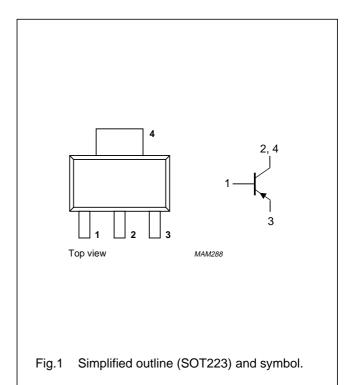
- Class-B video output stages of colour television receivers.
- General purpose high voltage circuits.

DESCRIPTION

PNP transistors in a SOT223 plastic package. NPN complements: BF720 and BF722.

PINNING

PIN	DESCRIPTION
1	base
2	collector
3	emitter
4	collector



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BF721		_	-300	V
	BF723		_	-250	V
V _{CEO}	collector-emitter voltage	open base			
	BF721		_	-300	V
	BF723		_	-250	V
I _{CM}	peak collector current		_	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	_	1.2	W
h _{FE}	DC current gain	$I_C = -25 \text{ mA}; V_{CE} = -20 \text{ V}$	50	_	
C _{re}	feedback capacitance	$I_C = i_c = 0$; $V_{CE} = -30 \text{ V}$; $f = 1 \text{ MHz}$	_	2.5	pF
f _T	transition frequency	$I_C = -10 \text{ mA}; V_{CE} = -10 \text{ V}; f = 100 \text{ MHz}$	60	_	MHz

Philips Semiconductors Product specification

PNP high-voltage transistors

BF721; BF723

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BF721		_	-300	V
	BF723		_	-250	V
V _{CEO}	collector-emitter voltage	open base			
	BF721		_	-300	V
	BF723		_	-250	V
V _{EBO}	emitter-base voltage	open collector	_	-5	V
I _C	collector current (DC)		_	-50	mA
I _{CM}	peak collector current		_	-100	mA
I _{BM}	peak base current		_	-50	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	1.2	W
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	106	K/W
R _{th j-s}	thermal resistance from junction to soldering point	note 1	25	K/W

Note

CHARACTERISTICS

T_i = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = -200 V	_	-10	nA
		$I_E = 0$; $V_{CB} = -200 \text{ V}$; $T_j = 150 ^{\circ}\text{C}$	_	-10	μΑ
I _{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = -5 \text{ V}$	_	-50	nA
h _{FE}	DC current gain	$I_C = -25 \text{ mA}; V_{CE} = -20 \text{ V}$	-50	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -30 \text{ mA}; I_B = -5 \text{ mA}$	_	-0.6	V
C _{re}	feedback capacitance	$I_C = I_c = 0$; $V_{CE} = -30 \text{ V}$; $f = 1 \text{ MHz}$	_	2.5	pF
f _T	transition frequency	$I_C = -10 \text{ mA}; V_{CE} = -10 \text{ V}; f = 100 \text{ MHz}$	60	_	MHz

^{1.} Device mounted on printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see "Thermal considerations for SOT223 in the General part of handbook SC04".

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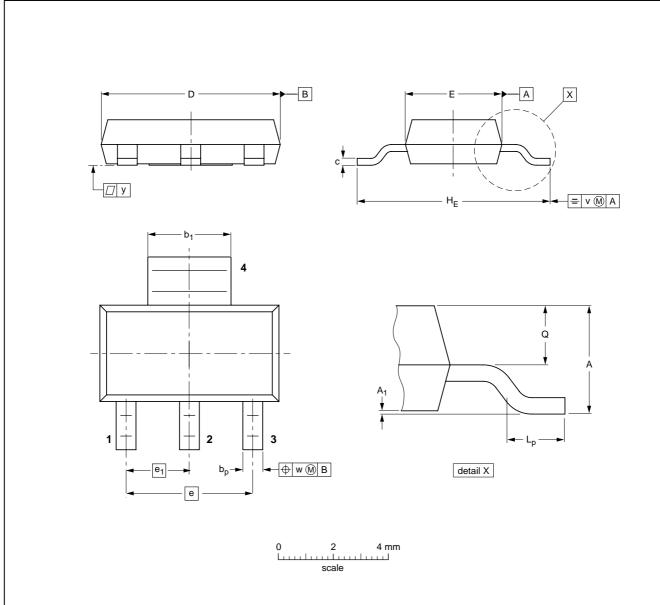
PNP high-voltage transistors

BF721; BF723

PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

SOT223



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	bp	b ₁	С	D	E	е	e ₁	HE	Lp	Q	v	w	у	
mm	1.8 1.5	0.10 0.01	0.80 0.60	3.1 2.9	0.32 0.22	6.7 6.3	3.7 3.3	4.6	2.3	7.3 6.7	1.1 0.7	0.95 0.85	0.2	0.1	0.1	

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT223						96-11-11 97-02-28

Philips Semiconductors Product specification

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DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.